CMSD4448

SUPER-MINI
HIGH SPEED
SWITCHING DIODE

SOT-323 CASE

Central™
Semiconductor Corp.

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMSD4448 type is a ultra-high speed silicon switching diode manufactured by the epitaxial planar process, in an epoxy molded super-mini surface mount package, designed for high speed switching applications.

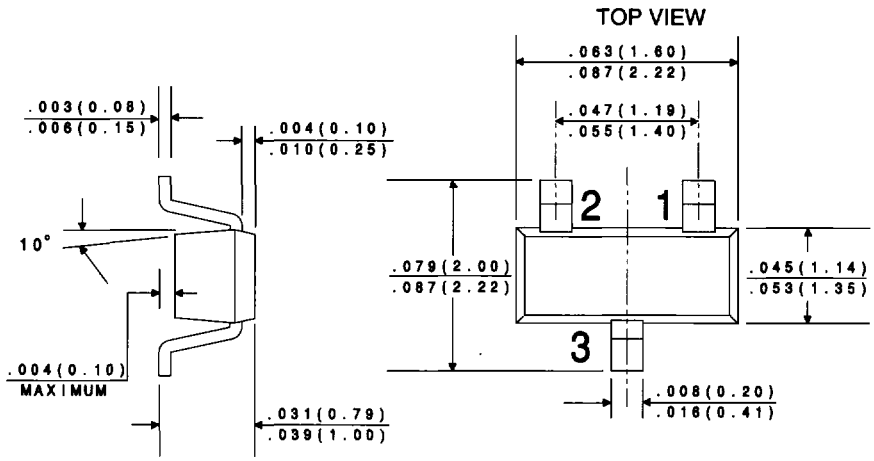
MAXIMUM RATINGS: (T_A=25°C)

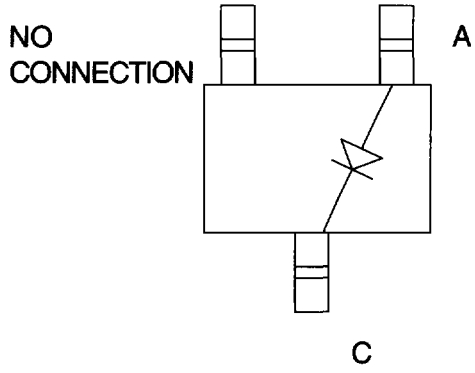
	SYMBOL		UNITS
Continuous Reverse Voltage	V_R	75	V
Peak Repetitive Reverse Voltage	V_{RRM}	100	V
Continuous Forward Current	I_F	250	mA
Peak Repetitive Forward Current	I_{FRM}	250	mA
Forward Surge Current, tp=1μsec.	I_{FSM}	4000	mA
Forward Surge Current, tp=1 sec.	I_{FSM}	1000	mA
Power Dissipation	P_D	250	mW
Operating and Storage Junction Temperature	T_J,T_{stg}	-65 to +150	°C
Thermal Resistance	Θ_{JA}	500	°C/W

ELECTRICAL CHARACTERISTICS: (T_A=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
V_{BR}	I_R=5.0μA	75		V
V_{BR}	I_R=100μA	100		V
I_R	V_R=20V		25	nA
V_F	I_F=5.0mA	0.62	0.72	V
V_F	I_F=100mA		1.0	V
C_T	V_R=0, f=1 MHz		4.0	pF
t_{rr}	I_R=I_F=10mA, R_L=100Ω, Rec. to 1.0mA		4.0	ns

All dimensions in inches (mm).





DATA SHEET

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